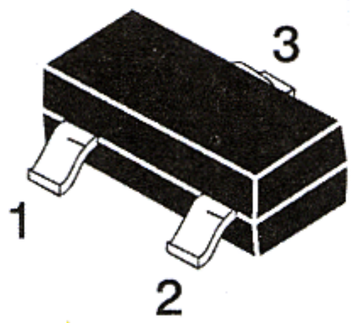
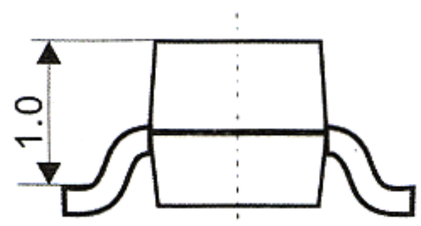
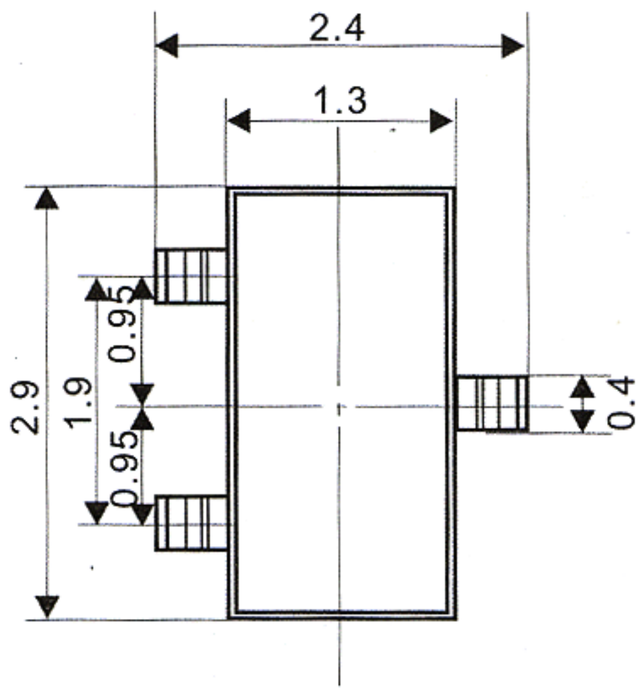
SOT-23 Plastic-Encapsulate Transistors

MMBTA55/56LT1 TRANSISTOR (PNP)

1.BASE
2.EMITTER
3.COLLECTOR







UNIT：mm

FEATURES

Power dissipation

PCM：0.225 W（Tamb=25℃）

Collector current

ICM：-0.5 A

Collector-base voltage

VCBO:MMBTA55:-60V
MMBTA56:-80V

Operating and storage junction temperature range

TJ,Tstg :-55℃ to+150℃

ELECTRICAL CHARACTERISTICS

(Tamp=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Drain-source Breakdown Voltage	$V_{(BR)CBO}$	I_C=-100μA, I_E=0	-60 -80		V
Collector Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-60 -80		
Emitter-base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-100μA,I_C=0	-4		
Collector Cut-off Current	I_{CBO}	V_{CB}=-60V,I_E=0 V_{CB}=-80V,I_E=0		-0.1 -0.1	μA
Collector Cut-off Current	I_{CEO}	V_{CE}=-50V,I_B=0 V_{CE}=-60V,I_B=0		-0.1 -0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-1V,I_C=-10mA	100		
	$h_{FE(2)}$	V_{CE}=-1V,I_C=-100mA	100		
Collector-emitter Saturation Voltage	V_{CEsat}	I_C=-100mA,I_B=-10mA		-0.25	V
Bsse -emitter Voltage	V_{BE}	V_{CE}=-1V,I_C=-100mA		-1.2	V
Transition Frequency	f_T	V_{CE}=-1V,I_C=-100mA f=100MHz	50		MHz

DEVICE MARKING : MMBTA55LT1:2H MMBTA56LT1:2G